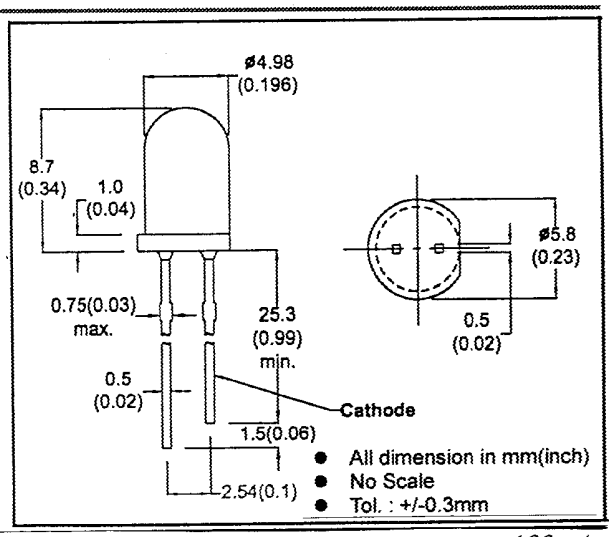
MICRO ELECTRONICS

MIB57TA-K

INFRARED EMITTING DIODE

DESCRIPTION

MIB57TA-J and MIB57TA-K are GaAlAs infrared emitting diode molded in a 5mm diameter clear transparent lens.



ABSOLUTE MAXIMUM RATINGS

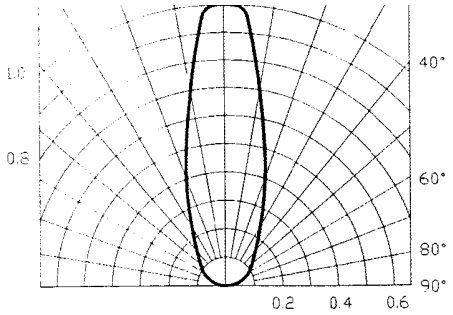
Forward Current (Continuous)	100mA
Pulse Forward Current	1A*
Reverse Voltage (Continuous)	6V
Power Dissipation	175mW
Operating Temperature Range	-40 to +100°C
Lead Soldering Temperature (1/16" from body)	260°C for 5 sec.

* Pulse Width = 10μs, Duty Ratio = 0.01.

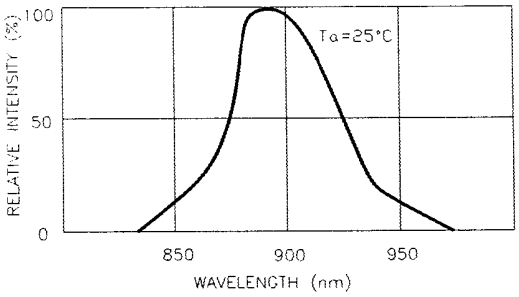
ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

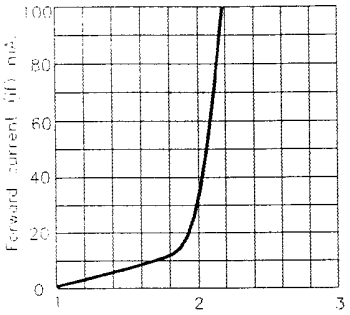
PARAMETER		SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Radiant Power Output	MIB57TA-J	Po	7.5	10		mW	IF=20mA
	MIB57TA-K		5.5	8		mW	IF=20mA
Forward Voltage	MIB57TA-J	VF		1.65	2	V	IF=10mA
	MIB57TA-K			1.65	2	V	IF=10mA
Reverse Current	MIB57TA-J	IR			100	μA	VR=4V
	MIB57TA-K				100	μA	VR=4V
Peak Wavelength	MIB57TA-J	$\lambda\rho$		880		nm	IF=20mA
	MIB57TA-K			880		nm	IF=20mA
Spectrum Line Half Width	MIB57TA-J	$\Delta\lambda$		80		nm	IF=20mA
	MIB57TA-K			80		nm	IF=20mA
Viewing Angle	MIB57TA-J	2θ 1/2		30		degree	IF=20mA
	MIB57TA-K			70		degree	IF=20mA

MICRO ELECTRONICS LTD.
38, Hung To Road, Microtron Bulding, Kwun Tong, Kowloon, Hong Kong.
Kwun Tong P.O. Box 69477 Hong Kong. Fax No. 2341 0321 Telex:43510 Micro Hx. Tel: 2343 0181-5



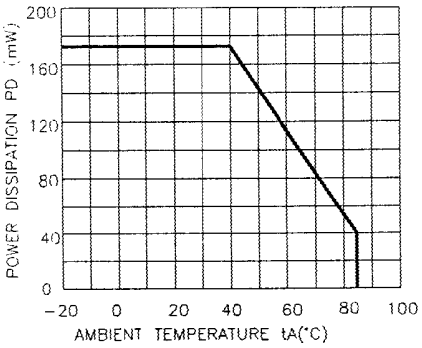
SPATIAL DISTRIBUTION



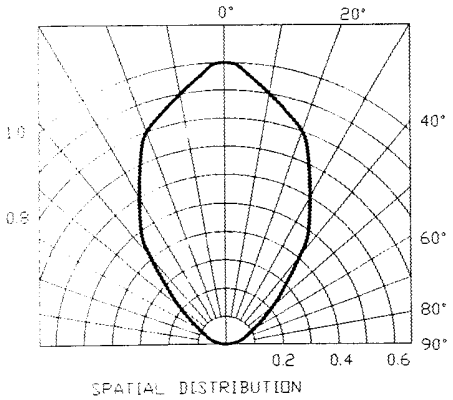


FORWARD CURRENTS VS.
FORWARD VOLTAGE

POWER DISSIPATION

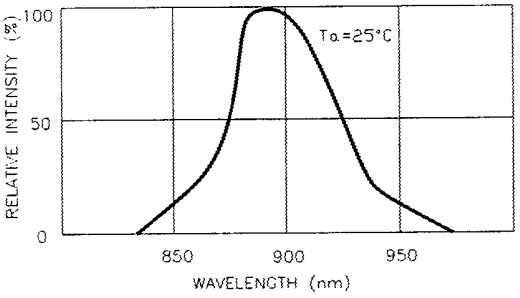


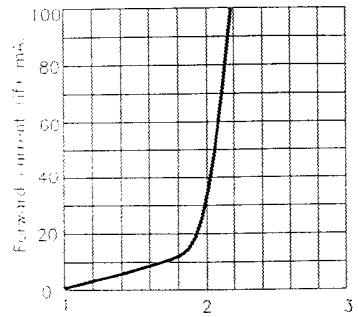
MIB57TA−K



SPATIAL DISTRIBUTION

RELATIVE INTENSITY VS.WAVELENGTH





FORWARD CURRENTS VS.
FORWARD VOLTAGE

POWER DISSIPATION